

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3576	((438/14) or (438/110) or (438/125) or (438/456)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/21 20:19
S96	2779	(platform table) same align\$6 same (liquid flow\$6)	USPAT	OR	ON	2005/09/21 17:58
S97	569	(platform table) with align\$6 with (liquid flow\$6)	USPAT	OR	ON	2005/03/09 18:44
S98	0	((platform table) with align\$6 with (liquid flow\$6)).ti.	USPAT	OR	ON	2005/03/09 18:45
S99	15	((platform table) with align\$6 with (liquid flow\$6)).ab.	USPAT	OR	ON	2005/03/09 18:48
S100	10	((platform table) same align\$6 same (liquid flow\$6) same (semiconductor wafer substrate ic integrated adj ciruit die dice)).ab.	USPAT	OR	ON	2005/03/09 18:50
S101	10	((platform table) same align\$6 same (liquid flow\$6) same ((semiconductor si silicon) near2 (wafer substrate) ic integrated adj ciruit die dice)).ab.	USPAT	OR	ON	2005/03/09 18:52
S102	160801	(semiconductor si silicon) near2 (wafer substrate)	USPAT	OR	ON	2005/03/09 18:51
S103	10	((platform table) same align\$6 same (liquid flow\$6) same (S102 ic integrated adj ciruit die dice)).ab.	USPAT	OR	ON	2005/03/09 18:52
S104	104	((platform table) same align\$6 same (liquid flow\$6) same (S102 ic integrated adj ciruit die dice))	USPAT	OR	ON	2005/03/09 18:52
S105	11	("5634267") or ("6219908") or ("6245595") or ("6258609") or ("6275051").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/23 18:57
S106	5	("5634267") or ("6219908") or ("6245595") or ("6258609") or ("6275051").PN.	USPAT	OR	OFF	2005/05/23 18:57
S107	15296	align\$6 with drop\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 15:07

S10 8	83822	surface adj tension	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 17:58
S10 9	2124260	chip wafer dice die package ic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 15:07
S11 0	2	S107 with S108 with S109	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:19
S11 1	4	S107 with S108 same S109	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:19
S11 2	9	S107 same S108 same S109	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:19
S11 3	7	S112 not S110	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:19
S11 4	6	S113 and (@ad < "20030705")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 16:53
S11 5	11	("5817242").URPN.	USPAT	OR	OFF	2005/05/23 19:39
S11 6	0	("5817242").ref.	USPAT	OR	OFF	2005/05/23 19:39
S11 7	11	("5817242").uref.	USPAT	OR	OFF	2005/05/23 19:39
S11 8	1	"5512131".PN.	USPAT; USOCR	OR	OFF	2005/05/25 16:39
S11 9	2125303	chip wafer dice die package ic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 12:12

S12 0	15305	align\$6 with drop\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 15:08
S12 1	83887	surface adj tension	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 15:07
S12 2	1460319	align\$6 selfalign\$6 self-align\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 12:09
S12 3	3488502	liquid\$6 fluid\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 15:08
S12 4	4197893	liquid\$6 fluid\$4 drop\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 15:09
S12 5	2337	S122 with S124 with S119	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 15:10
S12 6	3593147	chip wafer dice die package ic substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 15:10
S12 7	14932	S122 with S124 with S126	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 15:11
S12 8	90	S122 with S124 with S126 with S121	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 17:18
S12 9	79	S128 and (@ad < "20030705")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 17:18

S13 0	8418081	"10" and (@ad < "20030705")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 17:22
S13 1	83887	surface adj tension	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 17:18
S13 2	1460319	align\$6 selfalign\$6 self-align\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 17:18
S13 3	4197893	liquid\$6 fluid\$4 drop\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 17:18
S13 4	3593147	chip wafer dice die package ic substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 17:18
S13 5	90	S132 with S133 with S134 with S131	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 17:19
S13 6	4554980	via viahole throughhole hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 17:18
S13 7	2	S132 with S133 with S134 with S131 with S136	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 18:54
S13 8	103	S132 same S133 same S134 same S131 same S136	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 17:21
S13 9	96	S138 and (@ad < "20030705")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 19:02

S14 0	8	S132 with S133 with S134 with S131 same (hole cavity aperture opening space)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 19:01
S14 1	135	S132 same S133 same S134 same S131 same (hole cavity aperture opening space)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 19:43
S14 2	124	S141 and (@ad < "20030705")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 19:45
S14 3	29	S132 same S133 same S134 same S131 same (temperature celsius celcius centigrade degree heat\$4 thermal\$4 cool\$4) same (solidif\$4 cur\$4 setup set-up set\$4 adj up)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 19:52
S14 4	26	S143 and (@ad < "20030705")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 19:46
S14 5	3	S132 same S133 same S134 same S131 same (temperature celsius celcius centigrade degree heat\$4 thermal\$4 cool\$4) same (solidif\$4 cur\$4 setup set-up set\$4 adj up) same (agent additive add\$4 combin\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 19:55
S14 6	12	S132 same S133 same S134 same S131 same (temperature celsius celcius centigrade degree heat\$4 thermal\$4 cool\$4) same (solidif\$4 cur\$4 setup set-up set\$4 adj up) same (agent additive add\$4 combin\$4 resin fill\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 19:57
S14 7	6435	fixture near2 plate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 12:10
S14 8	373705	backgrind\$4 grind\$4 cmp planariz\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 16:43

S14 9	1762079	chip wafer dice die ic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 12:12
S15 0	1875414	chip wafer dice die ic (silicon si) near2 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 12:13
S15 1	40863	sigulat\$4 dicing dice	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 12:45
S15 2	24065	sigulat\$4 dicing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 12:13
S15 3	13	S147 and S148 and S150 and S152	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 12:13
S15 4	1416	known adj good adj die kgd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 18:35
S15 5	10634	burn-in burnin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 12:47
S15 6	3437186	test\$4 measur\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 12:47
S15 7	2	S147 and S148 and S154 and S155 and S156	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 12:49
S15 8	16	S147 and S154 and S155 and S156	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 13:25

S15 9	1724	wafer adj level near2 S156	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 13:26
S16 0	1	S147 same S159 same S154 same S155	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 13:28
S16 1	1	S147 same S159 same S154	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 13:26
S16 2	162290	(wafer circuit multichip multi adj chip) near2 S156	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 13:27
S16 3	162424	(wafer circuit multichip multi adj chip mcm) near2 S156	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 13:27
S16 4	22	S163 same S159 same S154 same S155	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 13:28
S16 5	3381	((438/14) or (438/110) or (438/125) or (438/456)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/21 20:19
S16 6	1	"5593903".PN.	USPAT; USOCR	OR	OFF	2005/05/25 16:39
S16 7	1	S166 and (singulat\$4 dic\$4)	USPAT; USOCR	OR	OFF	2005/05/25 16:44
S16 8	373705	backgrind\$4 grind\$4 cmp planariz\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 16:44
S16 9	0	S166 and (singulat\$4 dic\$4) and S168	USPAT; USOCR	OR	OFF	2005/05/25 16:53

S170	1416	known adj good adj die kgd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 16:52
S171	100	S170 and (singulat\$4 dic\$4) and S168	USPAT; USOCR	OR	ON	2005/05/25 16:53
S172	15305	align\$6 with drop\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 16:53
S173	83887	surface adj tension	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 16:53
S174	2125303	chip wafer dice die package ic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 16:53
S175	2	S172 with S173 with S174	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 16:53
S176	9	S172 same S173 same S174	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 16:53
S177	7	S176 not S175	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 16:53
S178	6	S177 and (@ad < "20030705")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 16:53
S179	178	S170 and (singulat\$4 dic\$4) and S168	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 16:54

S18 0	5	S170 same (singulat\$4 dic\$4) same S168	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 16:54
S18 1	0	("6861336").URPN.	USPAT	OR	OFF	2005/05/25 16:56
S18 2	0	("6861336").Uref.	USPAT	OR	OFF	2005/05/25 16:56
S18 3	1	"6013534".PN.	USPAT; USOCR	OR	OFF	2005/05/25 18:35
S18 4	1	"6582983".PN.	USPAT; USOCR	OR	OFF	2005/05/25 16:57
S18 5	1	"6013534".PN.	USPAT; USOCR	OR	OFF	2005/09/21 17:57
S18 6	1416	known adj good adj die kgd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 18:35
S18 7	0	S185 and S186	USPAT; USOCR	OR	OFF	2005/05/25 19:01
S18 8	1	S185 and (test\$4 measur\$4)	USPAT; USOCR	OR	OFF	2005/05/25 19:01
S18 9	0	S185 and (test\$4 measur\$4) and (burnin burn)	USPAT; USOCR	OR	OFF	2005/05/25 19:01
S19 0	0	"20020066523".PN.	USPAT; USOCR	OR	OFF	2005/09/21 17:58
S19 1	0	"20020066523".PN.	USPAT; USOCR	OR	OFF	2005/09/21 17:58
S19 2	2	"20020066523".PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 17:58
S19 3	1	S192 and (encapsulat\$5 resin epoxy)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 18:01
S19 4	5	(("5736780") or ("5927505") or ("6159770") or ("6081997") or ("5723900")).PN.	USPAT; USOCR	OR	OFF	2005/09/21 18:01
S19 5	320	((bond\$4 join\$4) with (second! addition\$4 multiple another) adj (wafer substrate die chip) same (encapsulat\$4 resin epoxy)).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 18:05

S19 6	141	(bond\$4 join\$4) with (second! addition\$4 multiple another) adj (wafer substrate die chip) with (encapsulat\$4 resin epoxy) near4 (between fill\$4 underfill\$4 gap space)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 18:06
S19 7	141	((bond\$4 join\$4) with (second! addition\$4 multiple another) adj (wafer substrate die chip) with (encapsulat\$4 resin epoxy) near4 (between fill\$4 underfill\$4 gap space))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 18:07
S19 8	28	((bond\$4 join\$4) with (second! addition\$4 multiple another) adj (wafer substrate die chip) with (encapsulat\$4 resin epoxy) near4 (between fill\$4 underfill\$4 gap space)).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 18:18
S19 9	17	((mcm multichip adj module multi adj chip adj module) with (encapsulat\$4 resin epoxy) near4 (between fill\$4 underfill\$4 gap space)).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 18:20
S20 0	115	((mcm multichip adj module multi adj chip adj module) with (encapsulat\$4 resin epoxy) near4 (between fill\$4 underfill\$4 gap space))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 18:20